Nabiha Ben Sedrine

List of Publications by Year
in descending order

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70	1,142	471371	434063
papers	citations	17 h-index	31 g-index

70	70	70	1706
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Multifunctional Materials: A Case Study of the Effects of Metal Doping on ZnO Tetrapods with Bismuth and Tin Oxides. Advanced Functional Materials, 2017, 27, 1604676.	7.8	140
2	Hybridization of Zinc Oxide Tetrapods for Selective Gas Sensing Applications. ACS Applied Materials & Interfaces, 2017, 9, 4084-4099.	4.0	135
3	Correlation between microstructure and optical properties of nano-crystalline TiO2 thin films prepared by solâ€“gel dip coating. Applied Surface Science, 2010, 257, 670-676.	3.1	105
4	Elaboration and characterization of nanocrystalline TiO2 thin films prepared by solâ€“gel dip-coating. Surface and Coatings Technology, 2011, 206, 243-249.	2.2	53
5	Temperature dependent effective mass in AlGaN/GaN high electron mobility transistor structures. Applied Physics Letters, 2012, 101, .	1.5	44
6	Buckminsterfullerene hybridized zinc oxide tetrapods: defects and charge transfer induced optical and electrical response. Nanoscale, 2018, 10, 10050-10062.	2.8	44
7	Y_xAl_{1â^'x}N thin films. Journal Physics D: Applied Physics, 2012, 45, 422001.	1.3	42
8	Solâ€“gel synthesis, characterization and optical properties of mercury-doped TiO2 thin films deposited on ITO glass substrates. Applied Surface Science, 2011, 257, 9103-9109.	3.1	34
9	Infrared to vacuum-ultraviolet ellipsometry and optical Hall-effect study of free-charge carrier parameters in Mg-doped InN. Journal of Applied Physics, 2013, 113, .	1.1	22
10	Luminescence studies on green emitting InGaN/GaN MQWs implanted with nitrogen. Scientific Reports, 2015, 5, 9703.	1.6	19
11	Photoluminescence studies of a perceived white light emission from a monolithic InGaN/GaN quantum well structure. Scientific Reports, 2015, 5, 13739.	1.6	19
12	Luminescence studies on SnO2 and SnO2:Eu nanocrystals grown by laser assisted flow deposition. Physical Chemistry Chemical Physics, 2015, 17, 13512-13519.	1.3	19
13	YAG:Dy â€“ Based single white light emitting phosphor produced by solution combustion synthesis. Journal of Luminescence, 2017, 183, 251-258.	1.5	19
14	Probing surface states in C₆₀decorated ZnO microwires: detailed photoluminescence and cathodoluminescence investigations. Nanoscale Advances, 2019, 1, 1516-1526.	2.2	18
15	Effect of nitrogen on the GaAs0.9â^'xNxSb0.1 dielectric function from the near-infrared to the ultraviolet. Applied Physics Letters, 2010, 97, 201903.	1.5	17
16	Study of damage formation and annealing of implanted III-nitride semiconductors for optoelectronic devices. Nuclear Instruments & Methods in Physics Research B, 2016, 379, 251-254.	0.6	17
17	Photoluminescence investigations of ZnO micro/nanostructures. Materials Today Chemistry, 2020, 16, 100243.	1.7	17
18	Effect of Mg doping on the structural and free-charge carrier properties of InN films. Journal of Applied Physics, 2014, 115, 163504.	1.1	16

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19	Eu Activation inÎ²-Ga2O3MOVPE Thin Films by Ion Implantation. ECS Journal of Solid State Science and Technology, 2019, 8, Q3097-Q3102.	0.9	15
20	ZnAl2O4 decorated Al-doped ZnO tetrapodal 3D networks: microstructure, Raman and detailed temperature dependent photoluminescence analysis. Nanoscale Advances, 2020, 2, 2114-2126.	2.2	15
21	Spectroscopic ellipsometry study of GaAs1â^'xBix material grown on GaAs substrate by atmospheric pressure metal-organic vapor-phase epitaxy. Applied Physics Letters, 2009, 95, 011910.	1.5	14
22	Photoluminescence studies of 2DEG confinement in InAs ultrathin layer introduced in GaAs/AlGaAs structure. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2134-2138.	1.3	14
23	Annealing temperature effect on the properties of mercury-doped TiO2 films prepared by solâ€“gel dip-coating technique. Applied Surface Science, 2011, 257, 5529-5534.	3.1	14
24	Structural and optical characterization of Gd_2SiO_5 crystalline fibres obtained by laser floating zone. Optical Materials Express, 2017, 7, 868.	1.6	14
25	Eu-Doped AlGaN/GaN Superlattice-Based Diode Structure for Red Lighting: Excitation Mechanisms and Active Sites. ACS Applied Nano Materials, 2018, 1, 3845-3858.	2.4	14
26	Spectroscopic Analysis of Eu³⁺ Implanted and Annealed GaN Layers and Nanowires. Journal of Physical Chemistry C, 2015, 119, 17954-17964.	1.5	13
27	Fluctuating potentials in GaAs:Si nanowires: critical reduction of the influence of polytypism on the electronic structure. Nanoscale, 2018, 10, 3697-3708.	2.8	13
28	Shifting Lu2SiO5 crystal to eutectic structure by laser floating zone. Journal of the European Ceramic Society, 2018, 38, 2059-2067.	2.8	13
29	Infrared dielectric functions and optical phonons of wurtzite Y_xAl_{1â^'x}N (0â€‰â€‰â©½â€‰â€‰xâ€‰â€‰â©½â€‰â€‰0.22). Journal Phys 48, 415102.	2.8	12
30	Spectroscopic analysis of LYSO:Ce crystals. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2017, 172, 163-167.	2.0	12
31	Optoelectronic Characterization of ZnO Nanorod Arrays Obtained by Pulse Electrodeposition. Journal of the Electrochemical Society, 2018, 165, D595-D603.	1.3	12
32	Analyzing ab initio infrared spectra and electronic properties of polyethylenimine water complexes in the solid state. Computational and Theoretical Chemistry, 2010, 945, 27-32.	1.5	11
33	Bandgap Engineering and Optical Constants of YxAl1-xN Alloys. Japanese Journal of Applied Physics, 2013, 52, 08JM02.	0.8	11
34	Europium-Implanted AlN Nanowires for Red Light-Emitting Diodes. ACS Applied Nano Materials, 2022, 5, 972-984.	2.4	11
35	Clustering and Morphology Evolution of Gold on Nanostructured Surfaces of Silicon Carbide: Implications for Catalysis and Sensing. ACS Applied Nano Materials, 2021, 4, 1282-1293.	2.4	10
36	Spectroscopic ellipsometry analysis of GaAs1â^'xNx layers grown by molecular beam epitaxy. Materials Science and Engineering C, 2008, 28, 640-644.	3.8	9

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37	Observation of many-body Coulomb interaction effects on the photoluminescence spectra of InAs/GaAs quantum dots. Applied Surface Science, 2008, 254, 3125-3129.	3.1	9
38	Spectroscopic analysis of the NIR emission in Tm implanted AlxGa1-xN layers. Journal of Applied Physics, 2016, 120, 081701.	1.1	9
39	Optical investigations of europium ion implanted in nitride-based diode structures. Surface and Coatings Technology, 2018, 355, 40-44.	2.2	9
40	Luminescent silver nanoclusters decorated on ZnO tetrapods: a detailed understanding of their role in photoluminescence features. Journal of Materials Chemistry C, 2021, 9, 7014-7026.	2.7	9
41	Multiple optical centers in Eu-implanted AlN nanowires for solid-state lighting applications. Applied Physics Letters, 2018, 113, 201905.	1.5	8
42	Enhancing the luminescence yield of Cr3+ in Î² -Ga2O3 by proton irradiation. Applied Physics Letters, 2022, 120, .	1.5	8
43	Rapid thermal annealing effects on the optical properties of GaAs0.9â‾xNxSb0.1 structures grown by MBE. Materials Science in Semiconductor Processing, 2015, 29, 331-336.	1.9	7
44	Substrate and Mg doping effects in GaAs nanowires. Beilstein Journal of Nanotechnology, 2017, 8, 2126-2138.	1.5	7
45	Hierarchical Aerographite 3D flexible networks hybridized by InP micro/nanostructures for strain sensor applications. Scientific Reports, 2018, 8, 13880.	1.6	7
46	Interplay between thin silver films and epitaxial graphene. Surface and Coatings Technology, 2020, 381, 125200.	2.2	6
47	Deep Defects Annihilation in GaAs1-xNx Layers by Si-doping. American Journal of Applied Sciences, 2007, 4, 19-22.	0.1	6
48	GaN:Pr³⁺ nanostructures for red solid state light emission. RSC Advances, 2014, 4, 62869-62877.	1.7	5
49	Correction to â€œSpectroscopic Analysis of Eu³⁺ Implanted and Annealed GaN Layers and Nanowiresâ€• Journal of Physical Chemistry C, 2016, 120, 6907-6908.	1.5	5
50	Exploring swift-heavy ion irradiation of InGaN/GaN multiple quantum wells for green-emitters: the use of Raman and photoluminescence to assess the irradiation effects on the optical and structural properties. Journal of Materials Chemistry C, 2021, 9, 8809-8818.	2.7	5
51	Ellipsometric investigation of porous silicon layers for the design of a DBR. EPJ Applied Physics, 2008, 43, 87-91.	0.3	4
52	Optical properties of GaAs0.9-xNxSb0.1 alloy films studied by spectroscopic ellipsometry. Thin Solid Films, 2011, 519, 2838-2842.	0.8	4
53	Structural, optical, electrical and morphological study of transparent p-NiO/n-ZnO heterojunctions grown by PLD. Proceedings of SPIE, 2015, , .	0.8	4
54	Modelling of Optical Damage in Nanorippled ZnO Produced by Ion Irradiation. Crystals, 2019, 9, 453.	1.0	4

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55	Eu3+ optical activation engineering in Al Ga1-N nanowires for red solid-state nano-emitters. Applied Materials Today, 2021, 22, 100893.	2.3	4
56	Iridium(III)porphyrin arrays with tuneable photophysical properties. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2020, 235, 118309.	2.0	4
57	Optical constants and critical-point parameters of GaAs1-xSbxalloy films grown on GaAs. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 833-836.	0.8	2
58	Defect luminescence in oxides nanocrystals grown by laser assisted techniques. , 2015, , .		2
59	Nanosensors: Multifunctional Materials: A Case Study of the Effects of Metal Doping on ZnO Tetrapods with Bismuth and Tin Oxides (Adv. Funct. Mater. 6/2017). Advanced Functional Materials, 2017, 27, .	7.8	2
60	Silver nanoparticle array on weakly interacting epitaxial graphene substrate as catalyst for hydrogen evolution reaction under neutral conditions. Applied Physics Letters, 2021, 119, 153902.	1.5	2
61	Optical properties of GaInNAsSb/GaAs/GaAs1â^'xNx (xâ‰ˆ10%) saturable absorber quantum wells. Applied Surface Science, 2008, 254, 7122-7126.	3.1	1
62	Optical properties of InN/In_{0.73}Ga_{0.27}N multiple quantum wells studied by spectroscopic ellipsometry. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1629-1632.	0.8	1
63	Quantum well intermixing and radiation effects in InGaN/GaN multi quantum wells. , 2016, , .		1
64	Photoluminescence study of the GaAs barrier effect on GaAs/GaInAs/GaAs quantum wells. , 2007, , .		0
65	Optical Constants of As-grown and RTA GaAs1-xNx Layers Analysed by Spectroscopic Ellipsometry. , 2007, , .		0
66	Redistribution of nitrogen localized states in GaAsN layer doped Silicon. EPJ Applied Physics, 2007, 38, 221-225.	0.3	0
67	Abnormal optical behaviour of InAsSb quantum dots grown on GaAs substrate by molecular beam epitaxy. Materials Science and Engineering C, 2008, 28, 918-922.	3.8	0
68	Strain effects of InP/Si and InP/porous Si studied by spectroscopic ellipsometry. EPJ Applied Physics, 2008, 42, 99-102.	0.3	0
69	Infrared ellipsometry and near-infrared-to-vacuum-ultraviolet ellipsometry study of free-charge carrier properties in In-polar p-type InN. Materials Research Society Symposia Proceedings, 2012, 1396, .	0.1	0
70	Spectroscopic Ellipsometry of AP-MOVPE-Grown GaAs1 â^' x Bi x Dilute Alloys. Springer Series in Materials Science, 2013, , 167-179.	0.4	0